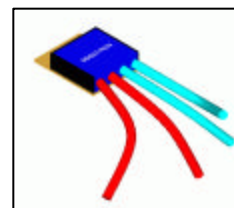


TECHNICAL DATA
PART NUMBER: SEN-4717



**SCHOTTKY BATTERY DISCHARGE
BYPASS DIODE**

DESCRIPTION: BATTERY DISCHARGE BYPASS SILICON SCHOTTKY DIODE.

MAXIMUM RATINGS

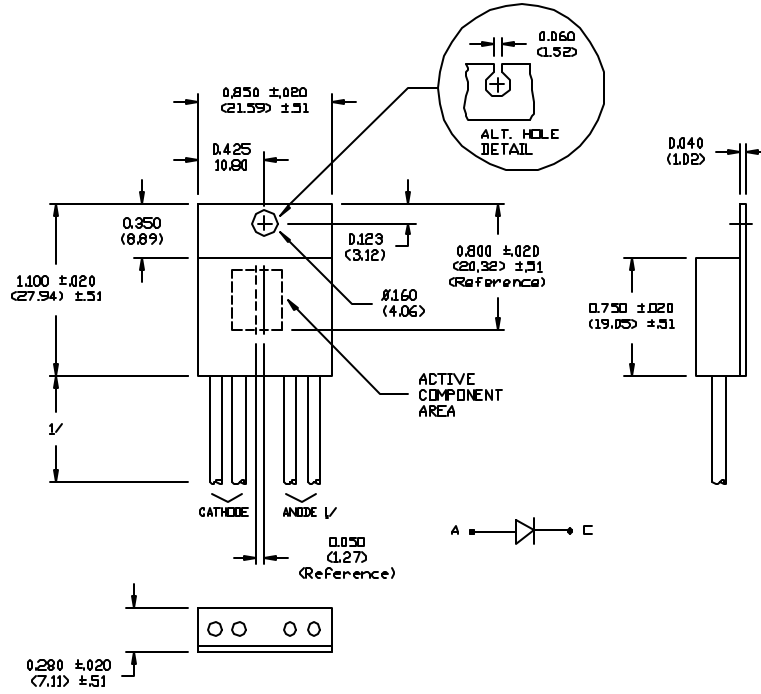
All ratings are at $T_A = 25^{\circ}\text{C}$ unless otherwise specified.

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV)	-	-	-	30	Vdc(pk)
Average DC Output Current (I_o) $T_A = 100^{\circ}\text{C}$	-	-	-	100	Amps
Non-Repetitive Peak Single Cycle Surge Current (I_{FSM}), $T_A = 100^{\circ}\text{C}$	$t_p = 8.3$ ms Single Half Cycle Sine Wave	-	-	500	Amps(pk)
Operating Temp. (T_{op})		-	-	+175	$^{\circ}\text{C}$
Storage Temp. (T_{stg})		-	-	+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Maximum Forward Voltage (V_f)	$I_f = 33\text{A dc}$, $T_A = 25^{\circ}\text{C}$ (300 μsec pulse, duty cycle < 2%)	-	-	0.53	Volts
Maximum Forward Voltage (V_f)	$I_f = 50\text{A dc}$, $T_A = 25^{\circ}\text{C}$ (300 μsec pulse, duty cycle < 2%)	-	-	0.55	Volts
Maximum Forward Voltage (V_f)	$I_f = 100\text{A dc}$, $T_A = 25^{\circ}\text{C}$ (300 μsec pulse, duty cycle < 2%)	-	-	0.70	Volts
Maximum Forward Voltage (V_f)	$I_f = 50\text{A dc}$, $T_A = 100^{\circ}\text{C}$ (300 μsec pulse, duty cycle < 2%)	-	-	0.43 0.51	Volts
Maximum Forward Voltage (V_f)	$I_f = 50\text{A dc}$, $T_C = 100^{\circ}\text{C}$ (300 μsec pulse, duty cycle < 2%)	-	-	0.64	Volts
Maximum Instantaneous Reverse Current (I_r)	@ 30Vdc $T_A = 25^{\circ}\text{C}$	-	-	15 7.5 10	mA
Maximum Instantaneous Reverse Current (I_r)	@ 30Vdc $T_A = 100^{\circ}\text{C}$	-	-	300	mA
Thermal Resistance Junction to Case ($R_{\theta JC}$)	-	-	-	0.5	$^{\circ}\text{C/W}$

MECHANICAL DIMENSIONS: In inches/mm



TECHNICAL DATA

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